EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	51	"5121273"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 16:09
S2	34993	electrolytic near capacitor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 16:12
S3	2	electrolytic near capacitor and pores and solution and semiconductor near layer and energiz$5 and @ad<"20041019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 16:14
S4	68	electrolytic near capacitor and pores and solution and semiconductor near layer and @ad<"20041019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 16:16
S5	47	electrolytic near capacitor and pores same solution and semiconductor near layer and @ad<"20041019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 16:21
S6	34	electrolytic near capacitor and pores with solution and semiconductor near layer and @ad<"20041019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 16:22
S7	0	electrolytic near capacitor and pores with electrol$3 near solution and semiconductor near layer and @ad<"20041019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 16:29

S8	30	electrolytic near capacitor and pores with electrol$3 and semiconductor near layer and @ad<"20041019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 16:29
S9	0	electrolytic near capacitor and pores with electrol$3 with impregnat$3 and semiconductor near layer and @ad<"20041019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 16:29
S10	25	electrolytic near capacitor and pores with electrol$3 and impregnat$3 and semiconductor near layer and @ad<"20041019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 16:30
S12	18	"576416"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 17:45
S13	4	"576416".ap.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 17:45
S14	7	"391160".ap.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/07 18:05
S15	27	capacitor and pores with electrol$3 and impregnat $3 and semiconductor near layer and @ad<"20041019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/07 20:39
S16	174	tantalum CV and @ad<"20041019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/09/07 20:39
S17	139	tantalum CV and electrolytic near capacitor and @ad<"20041019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/09/07 20:39

S18	4	"576416".ap.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 15:28
S19	7	"391160".ap.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 15:30
S20	26	"4943892"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 15:34
S21	5	"02066922"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 15:40
S22	459581	impregnat$5 ratio and capacitor	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/11 17:00
S23	23	impregnat$5 ratio and capacitor	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/09/11 17:00
S24	12	("20030089197" | "20030172774" | "3866316" | "4084965" | "4187327" | "4856320" | "4907442" | "4994751" | "5682102" | "6165623").PN. OR ("6510358" | "6934146").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/09/11 17:08
S25	445	438/99.ccls. and @ad<"20031021"	US-PGPUB; USPAT; USOCR	OR	ON	2009/09/11 19:08
S26	6	electrolytic capacitor and 438/99.ccls. and @ad<"20031021"	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/09/11 19:09
S27	11	electrolytic capacitor and 361/510.ccls. and @ad<"20031021"	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/09/11 19:10
S28	1	("4780796").PN.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/11 19:31
S29	130	naito-kazumi.in.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/11 19:31

S30	8	impregnat$5 ratio and naito-kazumi.in.	US-PGPUB; USPAT; USOCR; FPRS	ADJ	ON	2009/09/11 19:32
S31	1	impregnat$5 ratio and tamura-katutoshi.in.	US-PGPUB; USPAT; USOCR; FPRS	ADJ	ON	2009/09/11 19:37
S32	5	"02092864"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/11 19:39
S33	1	WO "2002092864"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2009/09/11 19:44
S34	13	impregnat$5 near ratio and showa denko	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2009/09/11 19:52
S35	22	impregnat$5 near ratio and electrolytic adj capacitor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2009/09/11 19:55
S36	0	"2003133256"	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/11 20:00
S38	2	"2003133256"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 20:04
S39	3	"2003243258"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 20:05
S40	3	"11074157"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 20:06

S41	5	"6088218"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 20:09
S42	68	hamada-takahiro.in.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/11 20:19
S43	0	"2003133256"	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/11 21:30
S44	4	"576416".ap.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/11 21:37
S45	4	"6934146"	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/11 22:38
S46	121	pore with etch$3 and electrolytic near capacitor and @ad<"20031023"	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/11 23:18
S47	314681	pore wth size with etch$3 and electrolytic near capacitor and @ad<"20031023"	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/11 23:22
S48	16	pore with size with etch$3 and electrolytic near capacitor and @ad<"20031023"	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/11 23:22
S49	0	pore with size near4 "200" with etch$3 and electrolytic near capacitor and @ad<"20031023"	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/09/11 23:23
S50	0	pore with size near4 "200" with etch$3 and electrolytic near capacitor and @ad<"20031023"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 23:24
S51	3	pore with size near4 microns with etch$3 and electrolytic near capacitor and @ad<"20031023"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 23:24
S52	6	pore with microns with etch$3 and electrolytic near capacitor and @ad<"20031023"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 23:25

S53	7	pore same microns with etch$3 and electrolytic near capacitor and @ad<"20031023"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 23:26
S54	13	pore same microns same etch$3 and electrolytic near capacitor and @ad<"20031023"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 23:27
S55	22	pore same microns and etch$3 and electrolytic near capacitor and @ad<"20031023"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/11 23:29
S56	115	pore etch$3 foil and electrolytic near capacitor and @ad<"20031020"	US-PGPUB; USPAT; USOCR; FPRS	SAME	ON	2009/09/11 23:41
S57	15	pore depth etch$3 foil and electrolytic near capacitor and @ad<"20031020"	US-PGPUB; USPAT; USOCR; FPRS	SAME	ON	2009/09/11 23:53

EAST Search History (Interference)

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